(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
10 August 2006 (10.08.2006)

PCT

(10) International Publication Number
WO 2006/082466 A1

(51) International Patent Classification:
H01L 21/324 (2006.01) *H01L 21/28* (2006.01)

(21) International Application Number:
PCT/IB2005/000434

(22) International Filing Date: 3 February 2005 (03.02.2005)

(25) Filing Language: English

(26) Publication Language: English

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

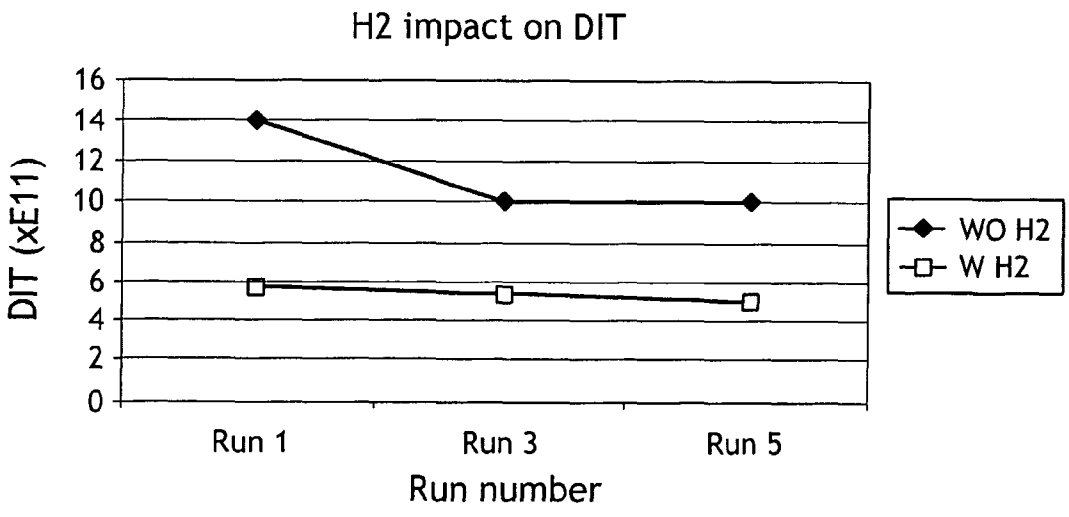
(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declaration under Rule 4.17:
— *of inventorship (Rule 4.17(iv))*

Published:
— *with international search report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: METHOD FOR REDUCING THE TRAP DENSITY IN A SEMICONDUCTOR WAFER



(57) Abstract: The invention concerns a method for reducing the trap density at an interface between an active layer of a multilayer semiconductor wafer and an insulating layer buried within said multilayer wafer under said active layer, said method comprising carrying out in a controlled atmosphere a high temperature thermal treatment to said multilayer wafer, said thermal treatment comprising an oxidation phase carried out in a controlled atmosphere comprising at least an oxidizing species at an oxidation temperature, and resulting in a capping of the surface of said wafer with a capping oxide layer, said method further comprising after said thermal treatment a deoxidation operation to remove said capping oxide layer created during said oxidation phase, characterized in that during said thermal treatment and after said oxidation phase said controlled atmosphere is controlled so as to comprise in a generally neutral atmosphere at least a species whose ions can migrate into the depth of said wafer down to said interface where reduction of the trap density is desired.

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